

Operational Experience and Performance with the ATLAS Pixel detector at the Large Hadron Collider at CERN

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The ATLAS Detector





The ATLAS tracking detector, situated most closely to the interaction point, consists of:

- the Transition Radiation Tracker (TRT)
- the Silicon Strip Detector (SCT)
- the Pixel Detector (PIX/IBL)

all situated within the ATLAS solenoid



Introduction: The ATLAS Pixel Detector

- The initial pixel detector had three barrel layers (innermost: B-layer) and three disks on each side
- IBL upgrade inserted a fourth innermost layer of smaller pitched pixels (2013/14 shutdown)
- In total about 92 million channels

	PIXEL (three outer layers + disks)	IBL (innermost layer)
Sensor Technology	n+-in-n (only planar)	n+-in-n/n+-in-p (planar/3D)
Sensor Thickness	250 µm	200/230 µm
Pixel Size	50x400 µm²	50x250 µm ²
Front End Technology	250 nm CMOS	130 nm CMOS
Radiation Hardness	50 Mrad 10 ¹⁵ n _{eq} /cm ²	250 Mrad 5x10 ¹⁵ n _{eq} /cm ²
Radii	~5, 9, and 12 cm	3.3 cm



Run 2 Operational Experience





Facing the Challenge: Run 2 Operational Conditions

- For Run 2 the tails of average pile-up distributions extended to over 60 interactions (top)
- Instantaneous luminosity doubled w.r.t. specifications and reached 2x10³⁴ cm²s⁻¹
 → challenging conditions for Pixel modules designed for half this value
- Delivered up to 70 fb⁻¹ per year and about 160 fb⁻¹ in Run 2 overall (bottom)
- Level-1 trigger rate increased to about 85 kHz
- → keep read-out occupancy within margins and mitigate desynchronisation despite high pile-up events to ensure good data quality







Detector Operation during Run 2

- Desynchronisation errors below 1%, despite increasing luminosity (top)
- Increased thresholds to mitigate bandwidth saturation caused by higher pile-up (bottom left)
- Threshold modifications (eta dependent) closely monitored to ensure no deterioration of track efficiency (bottom right)
- Dead-time below 0.2% (2018), DQ efficiency at 99.5% (in 2018: 99.8%) and less than 5% non-operational modules → excellent performance despite age and radiation





Radiation Damage and Modelling thereof

→ Also see recording of talk by T. Dado today morning in this session





IBL Retuning

- Change of transistor leakage current due to Total Ionising Dose (TID) known in IBM 130 nm CMOS technology → retuning of IBL charge response (ToT, top right) and threshold (bottom right) after irradiation
- By retuning every ~5 fb⁻¹ the ToT mostly stays within 0.5 bunch crossings and the threshold within 100 electrons (green bands)



TID effect on electronics: CERN Yellow Reports: Monographs, CERN-2021-001 (CERN, Geneva, 2021)

Tune 2 May

Tune 19 May

H- Tune 24 Jun.

- Tune 28 Jul.

- Tune 26 Sep

Tune 19 Oct

Tune 9 May

Tune 27 May

Tune 10 Aug

- Tune 4 Jul.

- Tune 5 Sep

- Tune 4 Oct.

42

Tune 9 May

Tune 27 May Tune 4 Jul.

- Tune 10 Aug.

800

Tune 19 May

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° °

34

650

36

- Tune 30 Apr

🚣 Tune 18 May

- Tune 3 Jun.

📥 Tune 18 Jul.

750

700

0

32

ATLAS Pixel Preliminary

Charge

tuning

30

ATLAS Pixel Preliminary

600

Threshold

2018

28

550

2018

IBL

oT [Bunch Cr

10

P0 1 [Bunch Crossing P0 90 80 1



Luminosity [fb⁻¹]

850 900 950 Average IBL Fluence I1 MeV neutron egy, cm⁻²

48 TID IMrad

Evolution of <dE/dx> and Cluster Size

- Increased radiation damage → less collected charge (shallow downwards slope in <dE/dx>) and hence smaller cluster size (\$\overline{\phi}\$, z)
- Increase in HV → full depletion and reducing threshold to mitigate effect of less charge
- Increasing threshold (e.g. B-layer in 2016) due to limitation in bandwidth
- End of Run 2 → set lower thresholds and increase high voltage → mitigate effects of radiation damage





IBL: Charge Collection Efficiency (CCE)

- Increasing integrated luminosity → radiation damage to sensor bulk → reduction of collected charge (top)
- At 160 fb⁻¹ only 70% of initial charge → very small impact also on tracking as can be seen in the evolution of twocluster resolution (bottom)
- End of Run 2: at 70% CCE for IBL modules MPV is about 10 ke⁻ with a 2 ke⁻ threshold (tuning)





Modelling Radiation Damage: Leakage Currents

- Leakage current easily accessible quantity to monitor radiation damage
- Modelled by Hamburg Model (input: temperature, annealing) with reweighting
- Slight over prediction at high fluences





Depletion Voltage

- Depletion voltage measured via cross-talk scans (before type inversion) and bias-voltage scans (after)
- B-layer (top) in good agreement with prediction at low fluences
- For IBL (bottom), the Hamburg model slightly overpredicts the depletion voltage for low fluences and underpredicts it for high fluences





Towards and into Run 3



(CÉRN)

Towards Run 3

- Detector is being kept cold during Long Shutdown 2 (LS2) in order to reduce reverse annealing → keep voltage required for full depletion as low as possible for B-layer and IBL
- For operations: the goal is to set the HV high enough to stay fully depleted for one year
- Leakage current prediction for IBL (right) and Pixel (not shown) are within power supply limits
- Additionally, we are investigating to what extent it is possible to increase the cooling and reduce the module temperatures





Single Event Upsets in IBL

- Charged particles crossing front-end can corrupt registers → detune module (make them noisy or silence them) and change module low voltage (top)
- Mechanism to retune the IBL global registers w/o introducing any additional busy-time implemented during Run 2
- For Run 3: also IBL pixel level registers will be reconfigured which has been briefly tested previously (bottom)
- Moreover, reconfiguration of Pixel (in contrast to IBL) modules was implemented
- → mitigate effects of radiation to front-end (increasing integrated luminosity per fill in Run 3)



G. Balbi et al., Measurements of Single Event Upset in ATLAS IBL, 2020 JINST 15 P06023



Optoboard Replacement

- Opto-electrical conversion between read-out equipment and modules done by optoboards
- Optoboards have laser diode arrays (VCSELs) and PIN diode arrays
- Failure of VCSELs about 2 years after installation → exact failure mode unknown but possibly linked to humidity
- First optoboard replacement before 2018 run and a replacement of all broken, suspicious, and B-layer optoboards was done in early 2021 to prevent failures in Run 3
- Additional sealing of the opto-boxes to shield optoboards against humidity (bottom)







Summary

- Despite the radiation damage and age, the ATLAS Pixel detector has delivered excellent performance
- We kept (and keep) the detector cold to prevent reverse annealing, ensuring that we can achieve full depletion throughout Run 3
- During LS2 we have taken actions to recover modules which have previously failed due to a broken optical connection and hope to have mitigated this issue for Run 3
- Radiation damage is closely being monitored and modelled and the results are vital input for decisions on Run 3 operational parameters
- Radiation damage results are also of interest for upgrade (ITk) and research (RD50) projects
- Ready for the LHC commissioning phase (pilot beams) and Run 3 (2022)



Thank you for your attention!



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Lorentz Angle Measurements

- Magnetic field deflects charges propagating in sensor → Lorentz angle
- Lorentz angle can be measured by studying cluster size vs. track incidence angle (top left)

1.7

1.6

1.5

Average cluste

- Simulation input: TCAD electric field maps (Chiochia model, top right)
- Lorentz angle changes with temperature, bias voltage, and fluence (bottom)
- Sensitivity to electric field → measure Lorentz angle and study electric field





Fluence-to-Luminosity Factors

- Deriving the fluence-to-luminosity conversion factors in z-dependence
- Exploiting the various measurements: leakage current, Lorentz angle, and depletion voltage
- For IBL, the z-dependance is predicted (Pythia + FLUKA/Geant4) to be shallower than measured



